Datasheet

Standard Products RadHard-by-Design **RHD5921** Analog Voltage Multiplexer 16-Channel, Buffered

www.aeroflex.com/RHDseries

March 4, 2015



FEATURES

- □ Single power supply operation at 3.3V to 5V
- □ Radiation performance
 - Total dose:

>1Mrad(Si); Dose rate = 50 - 300 rads(Si)/s

passion for performation

- ELDRS Immune
- SEL Immune

- >100 MeV-cm²/mg >10¹⁴ neutrons/cm²
- Neutron Displacement Damage
- □ Full military temperature range
- □ Low Power consumption when enabled
- □ CMOS analog switching allows rail to rail operation and low switch impedance
- □ Address bus (A0-3), and one enable line
- □ High input impedance
- Designed for aerospace and high reliability space applications
- □ Packaging Hermetic ceramic
 - 24-pin, 0.614"L x 0.300"W x 0.105"Ht SOIC
 - Typical Weight 2 grams

□ Aeroflex Plainview's Radiation Hardness Assurance Plan is DLA Certified to MIL-PRF-38534, Appendix G.

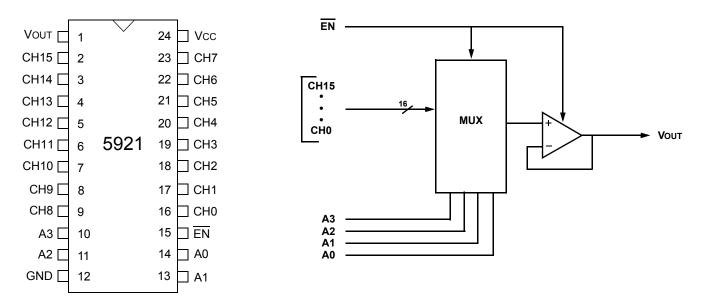
GENERAL DESCRIPTION

Aeroflex's RHD5921 is a radiation hardened, single supply, 16 channel buffered output multiplexer in a 24-pin SOIC package. The RHD5921 design uses specific circuit topology and layout methods to mitigate total ionizing dose effects and single event latchup. These characteristics make the RHD5921 especially suited for the harsh environment encountered in Deep Space missions. It is guaranteed operational from -55°C to +125°C. Available screened in accordance with MIL-PRF-38534 Class K, the RHD5921 is ideal for demanding military and space applications.

ORGANIZATION AND APPLICATION

The RHD5921 is a 16 to 1 CMOS buffered output voltage multiplexer. Channel selection is controlled by 4 bit binary addressing and an active low enable. Multiplexed voltages are buffered by a unity gain CMOS Rail-to-Rail amplifier. When the RHD5921 is disabled, the chip is put into a power-down state and the output is tri-stated.

The devices will not latch with SEU events to above 100 MeV-cm²/mg. Total dose degradation is minimal to above 1Mrad(Si). Displacement damage environments to neutron fluence equivalents in the mid 10^{14} neutrons per cm² range are readily tolerated. There is no sensitivity to low-dose rate (ELDRS) effects. SEU effects are application dependent.



Note:

1. Package and lid are electrically isolated from signal pads.

RHD5921: 16 CHANNEL BUFFERED ANALOG MUX

ABSOLUTE MAXIMUM RATINGS

Parameter	Range	Units
Case Operating Temperature Range	-55 to +125	°C
Storage Temperature Range	-65 to +150	°C
Supply Voltage (+Vcc)	+6.0	V
Digital Input Overvoltage (VEN, VA)	< Vcc +0.4 > GND -0.4	V V
Analog Input Overvoltage (CH0-CH15)	< Vcc +0.4 > GND -0.4	V
ESD Rating (MIL-STD-883, Method 3015, Class 2)	2,000 - 3,999	V

NOTICE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress rating only; functional operation beyond the "Operation Conditions" is not recommended and extended exposure beyond the "Operation Conditions" may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Typical	Units
+Vcc	Power Supply Voltage	3.3 to 5.0	V
VEN, VA	Logic Low Level	30% Vcc	V
Ven, Va	Logic High Level	70% Vcc	V

ELECTRICAL PERFORMANCE CHARACTERISTICS

(Tc = -55° C to $+125^{\circ}$ C, +Vcc = +5V -- Unless otherwise specified)

Parameter	Symbol	Conditions			Max	Units
Supply Current	+lcc	EN = 30% Vcc			5	mA
(+Vcc)	+ISBY	EN = 70% Vcc	EN = 70% Vcc			μA
	IAL	VA = 30% VCC	+25°C	-5	5	nA
Address Input Current		VA - 50% VCC	+125°C	-50	50	nA
(A0-A3)	Іан		+25°C	-5	5	nA
		VA = 70% VCC	+125°C	-50	50	nA
Enable Input Current (EN)	IENL		+25°C	-5	5	nA
		Ven = 30% Vcc	+125°C	-50	50	nA
	lenh		+25°C	-5	5	nA
		Ven = 70% Vcc	+125°C	-50	50	nA
Input Leakage Current (CH0-CH15)	+linlk	VIN = +5V, VEN =70% VCC,	+25°C	-5	5	nA
		Output and all unused MUX inputs under test = 0V	+125°C	-50	50	nA
Output Leakage Current		T	+25°C	-5	5	nA
(Vout)	+IOUTLK	Tri-state, VEN > 70% VCC	+125°C	-50	50	nA

ELECTRICAL PERFORMANCE CHARACTERISTICS (continued)

(Tc = -55°C TO +125°C, +Vcc = +5V -- UNLESS OTHERWISE SPECIFIED)

Parameter	Symbol	Conditions	Min	Max	Units
Output ON Voltage	Von1	VIN = 5 Volts, RL = 10K	4.8	5.1	V
	Von2	VIN = 5 Volts, RL = 1K		4.65	V
	Von3	VIN = 3.3 Volts, RL = 10K	3.2	3.4	V

SWITCHING CHARACTERISTICS

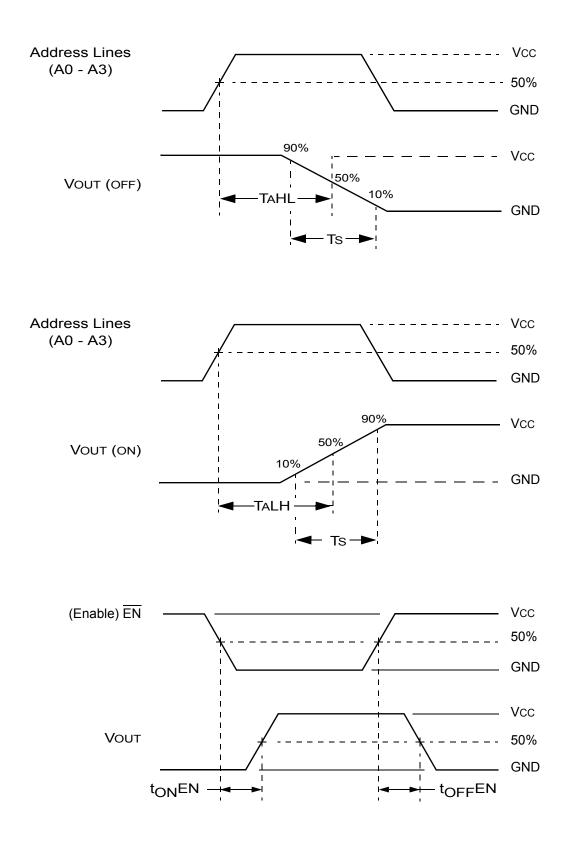
(Tc = -55°C TO +125°C, +Vcc = +5V -- UNLESS OTHERWISE SPECIFIED)

Parameter	Symbol	Conditions	Min	Max	Units
	TAHL	f = 10KHz, Vıℕ = 5 Volts, R∟ = 10K	1	3	us
Address to Output Delay (ON, OFF)	TALH	T = TORHZ, VIN = 5 VOILS, RL = TOR	1	3	us
Output Slew Rate	Ts		1.8	4	V/us
	TONEN	f = 10KHz V(h) = 5 V(alta D) = 1K	0.8	2.5	us
Enable to Output Delay	TOFFEN	f = 10KHz, ViN = 5 Volts, R∟ = 1K	100	350	ns

TRUTH TABLE (CH0 – CH15)

A3	A2	A1	A 0	EN	"ON" CHANNEL <u>1</u> /
Х	Х	Х	Х	Н	NONE
L	L	L	L	L	CH0
L	L	L	Н	L	CH1
L	L	Н	L	L	CH2
L	L	Н	Н	L	CH3
L	Н	L	L	L	CH4
L	Н	L	Н	L	CH5
L	Н	Н	L	L	CH6
L	Н	Н	Н	L	CH7
Н	L	L	L	L	CH8
Н	L	L	Н	L	CH9
н	L	Н	L	L	CH10
н	L	Н	Н	L	CH11
Н	Н	L	L	L	CH12
н	Н	L	Н	L	CH13
Н	Н	Н	L	L	CH14
Н	Н	Н	Н	L	CH15

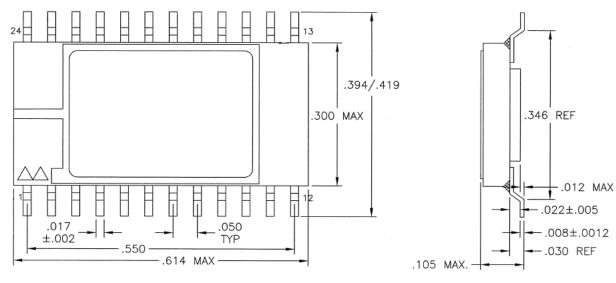
1/ Between (CH0-CH15) and VOUT



RHD5921 SWITCHING DIAGRAMS

ORDERING INFORMATION

Model	DLA SMD #	Screening	Package	
RHD5921-7	-	Commercial Flow, +25°C testing only		
RHD5921-S	-	Military Temperature, -55°C to +125°C Screened in accordance with the individual Test Methods of MIL-STD-883 for Space Applications		
RHD5921-201-1S	5962-1024302KXC	In accordance with DLA SMD	24-pin SOIC	
RHD5921-201-2S	5962-1024302KXA	in accordance with DEA SMD		
RHD5921-901-1S	5962H1024302KXC	In accordance with DLA Certified RHA Program Plan to		
RHD5921-901-2S	5962H1024302KXA	RHA Level "H", 1Mrad(Si)		



Note: Package and lid are electrically isolated from signal pads.

PACKAGE OUTLINE

EXPORT CONTROL:

This product is controlled for export under the U.S. Department of Commerce (DoC). A license may be required prior to the export of this product from the United States.

